

isc Silicon PNP Darlingtion Power Transistor

2SB1284

DESCRIPTION

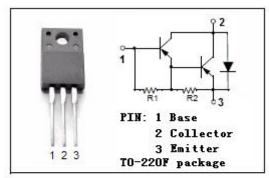
- · High DC Current Gain-
- : h_{FE}= 1500(Min.)@I_C= -5A
- · Low Collector Saturation Voltage-
 - : V_{CE(sat)}= -1.5V(Max)@I_C= -5A
- Good Linearity of hFE
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

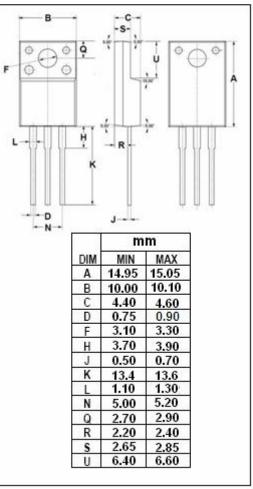
APPLICATIONS

- High power switching applications.
- · Hammer drive, pulse motor drive applications.



| SYMBOL | PARAMETER | VALUE | UNIT | |
|------------------|--------------------------------------|-----------------|--------------|--|
| V _{CBO} | Collector-Base Voltage | -100 | V | |
| V _{CEO} | Collector-Emitter Voltage | -100 | V | |
| V _{EBO} | Emitter-Base Voltage | -7 | V | |
| Ic | Collector Current-Continuous | -10 | А | |
| Ісм | Collector Current-Peak | -15 | А | |
| I _B | Base Current-Continuous | -0.8 | А | |
| I _{BM} | Base Current-peak | -1.5 | Α | |
| Pc | Collector Power Dissipation @ T₀=25℃ | 35 | W | |
| TJ | Junction Temperature | Temperature 150 | | |
| T _{stg} | Storage Temperature Range | -55~150 | $^{\circ}$ C | |







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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN | TYP. | MAX | UNIT | | |
|-----------------------|--------------------------------------|--|------|------|-------|------------|--|--|
| V _{(BR)CEO} | Collector-Emitter Breakdown Voltage | I _C = -30mA; I _B = 0 | -100 | | | V | | |
| V _{CE} (sat) | Collector-Emitter Saturation Voltage | I _C = -5A; I _B = -10mA | | | -1.5 | V | | |
| V _{BE} (sat) | Base-Emitter Saturation Voltage | I _C = -5A; I _B = -10mA | | | -2.0 | V | | |
| I _{CBO} | Collector Cutoff Current | V _{CB} = -100V; I _E = 0 | | | -100 | μА | | |
| I _{CEO} | Collector Cutoff Current | V _{CE} = -100V; R _{BE} = ∞ | | | -100 | μА | | |
| ІЕВО | Emitter Cutoff Current | V _{EB} = -7V; I _C = 0 | | | -5.0 | mA | | |
| h _{FE} | DC Current Gain | I _C = -5A; V _{CE} = -3V | 1500 | | 15000 | | | |
| f _T | Current-Gain—Bandwidth Product | I _C = -1A; V _{CE} = -10V | | 20 | | MHz | | |
| Switching Times | | | | | | | | |
| ton | Turn-on Time | | | | 1.0 | μ S | | |
| t _{stg} | Storage Time | I_{C} = -5.0A , I_{B1} = - I_{B2} = -10mA, V_{CC} \approx -40V; R_{L} = 6 Ω | | | 4.0 | μ S | | |
| tf | Fall Time | | | | 2.0 | μS | | |

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